

Amendments to the Claims

This listing of claims replaces all prior versions, and listings, of claims in the above-identified application:

Listing of Claims

1. **(Currently Amended)** A planarization method comprising:
 positioning a Group VIII metal-containing surface of a substrate to interface with
 a polishing surface, wherein the Group VIII metal is selected from the group of rhodium,
 iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;
 supplying a planarization composition in proximity to the interface; and
 planarizing the Group VIII metal-containing surface;
 wherein the planarization composition comprises a complexing agent selected
 from the group of a cyclic diene, an organic alkyl amine, and combinations thereof.
2. **(Original)** The method of claim 1 wherein the Group VIII metal is present in an amount
of about 50 atomic percent or more.
3. **(Original)** The method of claim 2 wherein the Group VIII metal-containing
surface of the substrate comprises a Group VIII metal in elemental form or an alloy
thereof.
4. **(Original)** The method of claim 3 wherein the Group VIII metal-containing surface
comprises elemental platinum or a platinum alloy.

5. **(Original)** The method of claim 4 wherein the Group VIII metal-containing surface comprises elemental platinum.
6. **(Currently Amended)** [[The method of claim 1]]A planarization method comprising:
positioning a Group VIII metal-containing surface of a substrate to interface with
a polishing surface, wherein the Group VIII metal is selected from the group of rhodium,
iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;
supplying a planarization composition in proximity to the interface;[[and]]
planarizing the Group VIII metal-containing surface;
wherein the planarization composition comprises a complexing agent selected
from the group of a cyclic diene, an organic amine, and combinations thereof[.]; and
wherein the planarization composition further comprises an oxidizing agent.
7. **(Original)** The method of claim 6 wherein the oxidizing agent is selected from the group consisting of a peroxide, a nitrate, a permanganate, and a combination thereof.
8. **(Original)** The method of claim 1 wherein the polishing surface comprises a polishing pad and the planarization composition comprises a plurality of abrasive particles.
9. **(Original)** The method of claim 1 wherein the planarization composition comprises a plurality of abrasive particles having a hardness of no greater than about 9 Mohs.
10. **(Original)** The method of claim 9 wherein the plurality of abrasive particles comprise CeO_2 , Al_2O_3 , SiO_2 , or combinations thereof.
11. **(Original)** The method of claim 1 wherein the substrate is a semiconductor substrate or substrate assembly.

12. **(Original)** The method of claim 1 wherein the Group VIII metal-containing surface is removed relative to an oxide layer at a selectivity ratio of at least about 10:1.
13. **(Original)** The method of claim 1 wherein the cyclic diene is selected from the group consisting of 1,5-cyclooctadiene (COD), 1,5-dimethyl-1,5-cyclooctadiene, and a combination thereof.
14. **(Currently Amended)** The method of claim 1 wherein the organic alkyl amine is selected from the group ethylamine, methylamine, triethylamine, trimethylamine, and combinations thereof.
15. **(Original)** The method of claim 1 wherein the polishing surface comprises a fixed abrasive article.
16. **(Currently Amended)** A planarization method comprising:
 - positioning a Group VIII metal-containing surface of a substrate to interface with a polishing surface, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;
 - supplying a planarization composition in proximity to the interface; and
 - planarizing the Group VIII metal-containing surface;
 - wherein the planarization composition comprises an organic alkyl amine and an organic chelating acid or salt thereof.
17. **(Original)** The method of claim 16 wherein the Group VIII metal is present in an amount of about 50 atomic percent or more.

18. **(Original)** The method of claim 16 wherein the Group VIII metal-containing surface comprises elemental platinum.
19. **(Original)** The method of claim 16 wherein the planarization composition further comprises an oxidizing agent.
20. **(Original)** The method of claim 19 wherein the oxidizing agent is selected from the group consisting of a peroxide, a nitrate, a permanganate, and a combination thereof.
21. **(Original)** The method of claim 16 wherein the polishing surface comprises a polishing pad and the planarization composition comprises a plurality of abrasive particles.
22. **(Original)** The method of claim 16 wherein the planarization composition comprises a plurality of abrasive particles having a hardness of no greater than about 9 Mohs.
23. **(Original)** The method of claim 22 wherein the plurality of abrasive particles comprise CeO_2 , Al_2O_3 , SiO_2 , or combinations thereof.
24. **(Original)** The method of claim 16 wherein the substrate is a semiconductor substrate or substrate assembly.
25. **(Original)** The method of claim 16 wherein the organic chelating acid is selected from the group consisting of acetic acid, ascorbic acid, citric acid, propenoic acid, tartaric acid, succinic acid, and combinations thereof.

26. **(Currently Amended)** The method of claim 16 wherein the organic alkyl amine is selected from the group consisting of ethylamine, methylamine, triethylamine, trimethylamine, and combinations thereof.
27. **(Original)** The method of claim 16 wherein the polishing surface comprises a fixed abrasive article.
28. **(Currently Amended)** A planarization method comprising:
 positioning a Group VIII metal-containing surface of a substrate to interface with a polishing surface, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;
 supplying a planarization composition in proximity to the interface; and
 planarizing the Group VIII metal-containing surface;
 wherein the planarization composition comprises a plurality of abrasive particles and a complexing agent; and further wherein a majority of the plurality of abrasive particles are CeO₂ abrasive particles.
29. **(Original)** The method of claim 28 wherein the Group VIII metal is present in an amount of about 50 atomic percent or more.
30. **(Original)** The method of claim 28 wherein the Group VIII metal-containing surface comprises elemental ruthenium.
31. **(Original)** The method of claim 28 wherein the planarization composition further comprises an oxidizing agent.

32. **(Original)** The method of claim 28 wherein the complexing agent is selected from the group consisting of an organic chelating acid, an organic amine, a cyclic diene, and combinations thereof.
33. **(Original)** The method of claim 32 wherein the organic chelating acid is selected from the group consisting of acetic acid, ascorbic acid, citric acid, propenoic acid, tartaric acid, succinic acid, and combinations thereof.
34. **(Currently Amended)** The method of claim 32 wherein the organic alkyl amine is selected from the group consisting of ethylamine, methylamine, triethylamine, trimethylamine, and combinations thereof.
35. **(Original)** The method of claim 32 wherein the cyclic diene is selected from the group consisting of 1,5-cyclooctadiene (COD), 1,5-dimethyl-1,5-cyclooctadiene, and a combination thereof.
36. **(Original)** The method of claim 28 wherein the polishing surface comprises a polishing pad.
37. **(Currently Amended)** A planarization method comprising:
 positioning a Group VIII metal-containing surface of a substrate to interface with a polishing surface, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;
 supplying a planarization composition in proximity to the interface; and
 planarizing the Group VIII metal-containing surface;
 wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic alkyl amine, [[an organic

chelating acid]]acetic acid, ascorbic acid, propenoic acid, succinic acid, salts of the acids,
and combinations thereof; and

further wherein the method is carried out in one step.

38. **(Currently Amended)** [[The method of claim 37]]A planarization method comprising:
positioning a Group VIII metal-containing surface of a substrate to interface with
a polishing surface, wherein the Group VIII metal is selected from the group consisting
of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;
supplying a planarization composition in proximity to the interface;[[and]]
planarizing the Group VIII metal-containing surface;
wherein the planarization composition comprises a complexing agent selected
from the group consisting of a cyclic diene, an organic amine, an organic chelating acid
and combinations thereof; and
further wherein the method is carried out in one step[.] ; and
wherein the planarization composition further comprises an oxidizing agent.

39. **(Currently Amended)** A planarization method comprising:
providing a semiconductor substrate or substrate assembly including at least one
region of a platinum-containing surface;
providing a polishing surface;
providing a planarization composition at an interface between the at least one
region of platinum-containing surface and the polishing surface;
and
planarizing the at least one region of platinum-containing surface;
wherein the planarization composition comprises a complexing agent selected
from the group consisting of a cyclic diene, an organic alkyl amine, and combinations
thereof.

40. **(Currently Amended)** [[The method of claim 39]] A planarization method comprising:
providing a semiconductor substrate or substrate assembly including at least one
region of a platinum-containing surface;
providing a polishing surface;
providing a planarization composition at an interface between the at least one
region of platinum-containing surface and the polishing surface; and
planarizing the at least one region of platinum-containing surface;
wherein the planarization composition comprises a complexing agent selected
from the group consisting of a cyclic diene, an organic amine, and combinations
thereof[.]; and
wherein the planarization composition further comprises an oxidizing agent.
41. **(Currently Amended)** A planarization method comprising:
providing a semiconductor substrate or substrate assembly including at least one
region of a platinum-containing surface;
providing a polishing surface;
providing a planarization composition at an interface between the at least one
region of platinum-containing surface and the polishing surface;
and
planarizing the at least one region of platinum-containing surface;
wherein the planarization composition comprises an organic alkyl amine and an
organic chelating acid or salt thereof.
42. **(Original)** The method of claim 41 wherein the planarization composition further
comprises an oxidizing agent.

43. **(Currently Amended)** A planarization method comprising:
- providing a semiconductor substrate assembly including at least one region of a platinum-containing surface;
 - providing a polishing surface;
 - providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface;
 - and
 - planarizing the at least one region of platinum-containing surface;
 - wherein the planarization composition comprises a plurality of abrasive particles and a complexing agent; and
 - further wherein a majority of the plurality of abrasive particles are CeO₂ abrasive particles.
44. **(Original)** The method of claim 43 wherein the planarization composition further comprises an oxidizing agent.
45. **(Original)** The method of claim 43 wherein the polishing surface comprises a polishing pad.
46. **(Currently Amended)** A planarization method comprising:
- providing a semiconductor substrate or substrate assembly including at least one region of a platinum-containing surface;
 - providing a polishing surface;
 - providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface; and
 - planarizing the at least one region of platinum-containing surface;

wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic alkyl amine, [[an organic chelating acid]]acetic acid, ascorbic acid, propenoic acid, succinic acid, salts of the acids, and combinations thereof; and

further wherein the method is carried out in one step.

47. **(Currently Amended)** [[The method of claim 44]] A planarization method comprising:

providing a semiconductor substrate or substrate assembly including at least one region of a platinum-containing surface;

providing a polishing surface;

providing a planarization composition at an interface between the at least one region of platinum-containing surface and the polishing surface; and

planarizing the at least one region of platinum-containing surface;

wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic amine, an organic chelating acid, and combinations thereof;[[and]]

further wherein the method is carried out in one step; and[[.]]

wherein the planarization composition further comprises an oxidizing agent.

48. **(Currently Amended)** A planarization method for use in forming a capacitor or barrier layer, the method comprising:

providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a Group VIII metal-containing layer formed over the patterned dielectric layer, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;

positioning a first portion of a polishing surface for contact with the Group VIII metal-containing layer;

providing a planarization composition in proximity to the contact between the polishing surface and the Group VIII metal-containing layer; and

planarizing the Group VIII metal-containing layer;

wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic alkyl amine, and combinations thereof.

49. (Original) [[The method of claim 48]] A planarization method for use in forming a capacitor or barrier layer, the method comprising:

providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a Group VIII metal-containing layer formed over the patterned dielectric layer, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;

positioning a first portion of a polishing surface for contact with the Group VIII metal-containing layer;

providing a planarization composition in proximity to the contact between the polishing surface and the Group VIII metal-containing layer; and

planarizing the Group VIII metal-containing layer;

wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic amine, and combinations thereof; and[.]

wherein the planarization composition further comprises an oxidizing agent.

50. **(Currently Amended)** A planarization method for use in forming a capacitor or barrier layer, the method comprising:

providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a Group VIII metal-containing layer formed over the patterned dielectric layer, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;

positioning a first portion of a polishing surface for contact with the Group VIII metal-containing layer;

providing a planarization composition in proximity to the contact between the polishing surface and the Group VIII metal-containing layer;

and

planarizing the Group VIII metal-containing layer;

wherein the planarization composition comprises an organic alkyl amine and an organic chelating acid or salt thereof.

51. **(Original)** The method of claim 50 wherein the planarization composition further comprises an oxidizing agent.

52. **(Currently Amended)** A planarization method for use in forming a capacitor or barrier layer, the method comprising:

providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a Group VIII metal-containing layer formed over the patterned dielectric layer, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;

positioning a first portion of a polishing surface for contact with the Group VIII metal-containing layer;

providing a planarization composition in proximity to the contact between the polishing surface and the Group VIII metal-containing layer;

and

planarizing the Group VIII metal-containing layer;

wherein the planarization composition comprises a plurality of abrasive particles and a complexing agent; and

further wherein a majority of the plurality of abrasive particles are CeO₂ abrasive particles.

53. **(Original)** The method of claim 52 wherein the planarization composition further comprises an oxidizing agent.

54. **(Original)** The method of claim 52 wherein the polishing surface comprises a polishing pad.

55. **(Currently Amended)** A planarization method for use in forming a capacitor or barrier layer, the method comprising:

providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a Group VIII metal-containing layer formed over the patterned dielectric layer, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;

positioning a first portion of a polishing surface for contact with the Group VIII metal-containing layer;

providing a planarization composition in proximity to the contact between the polishing surface and the Group VIII metal-containing layer;

and

planarizing the Group VIII metal-containing layer;

wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic alkyl amine, [[an organic chelating acid]]acetic acid, ascorbic acid, propenoic acid, succinic acid, salts of the acids, and combinations thereof; and

further wherein the method is carried out in one step.

56. **(Original)** [[The method of claim 55]] A planarization method for use in forming a capacitor or barrier layer, the method comprising:

providing a semiconductor substrate or substrate assembly having a patterned dielectric layer formed thereon and a Group VIII metal-containing layer formed over the patterned dielectric layer, wherein the Group VIII metal is selected from the group consisting of rhodium, iridium, ruthenium, osmium, palladium, platinum, and combinations thereof;

positioning a first portion of a polishing surface for contact with the Group VIII metal-containing layer;

providing a planarization composition in proximity to the contact between the polishing surface and the Group VIII metal-containing layer; and

planarizing the Group VIII metal-containing layer;

wherein the planarization composition comprises a complexing agent selected from the group consisting of a cyclic diene, an organic amine, an organic chelating acid, and combinations thereof;[[and]]

further wherein the method is carried out in one step; and

wherein the planarization composition further comprises an oxidizing agent.

57. **(Original)** The method of claim 55 wherein the polishing surface comprises a polishing pad.
58. **(Original)** The method of claim 55 wherein the polishing surface comprises a fixed abrasive article.